

Adaptive LED Current Filter For LED Lighting Preliminary datasheet

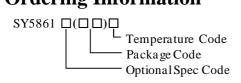
General Description

The SY5861 is an adaptive linear current regulator to eliminate low frequency current ripple targeting at LED lighting applications.

It is applied as a current filter to the output of a LED driver, especially single stage LED driver. It adopts adaptive control scheme and no additional electrical design is needed.

Reliable open/short LED protection and over thermal protection are all provided.

Ordering Information



Ordering Number	Package type	Note
SY5861FAC	SO8	

Features

- Current filter for single stage LED driver to eliminate current ripple
- Proprietary scheme for low power loss ≤2.5%
- Adaptive for wide output speculation: Output voltage range from 20V to 100V Output current ≤250mA
- Open LED Protection and Short LED protection
- Reliable short LED and Open LED protection
- Compact package: SO8

Applications

LED lighting

Typical Applications

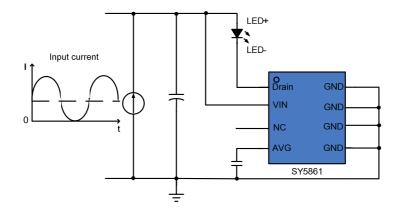
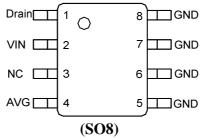


Figure 1. Schematic Diagram



Pinout (top view)



Top Mark: ATNxyz (device code: ATN, x=year code, y=week code, z= lot number code)

Pin Name	Pin Number	Pin Description
Drain	1	Drain of internal power MOSFET.
VIN	2	Power Supply
NC	3	NC.
AVG	4	Average current filter pin. Bypass a capacitor (100nF) to this pin and GND.
GND	5/6/7/8	Ground pin

Absolute Maximum Ratings (Note 1)

VIN	
Drain	
Power Dissipation, @ T _A = 25°C SO8	0.6W
Package Thermal Resistance (Note 2)	
SO8, θ_{JA}	88°C/W
SO8, θ_{JC}	45°C/W
Junction Temperature Range	
Lead Temperature (Soldering, 10 sec.)	260°C
Storage Temperature Range	

Recommended Operating Conditions

VIN, Drain ------20V~100V

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Electrical Characteristics

 $(V_{IN} = 12V, T_A = 25^{\circ}C \text{ unless otherwise specified})$

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Power Supply Section						
VIN turn-on threshold	$V_{VIN,ON}$			10		V
VIN turn-off threshold	$V_{VIN,OFF}$			8		V
VIN operating current	I_{VIN}			80		μA
Drain Section						
BV of internal MOSFET	V_{BV}			100		V
Thermal Section						
Thermal Shutdown Temperature	T_{SD1}	$V_{DRAIN} < 10V$		150		С
Thermal Shutdown Temperature	T_{SD2}	$V_{DRAIN} > 10V$		125		С
Thermal Hysteresis Temperature	T_{HYS}			25		С

Note 1: Stresses beyond the "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only. Functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

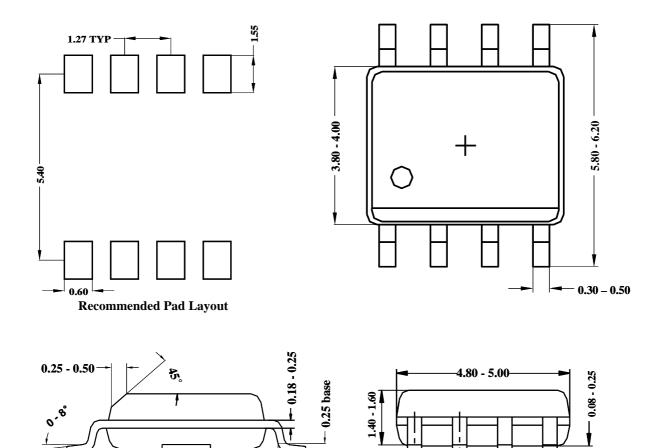
Note 2: Θ_{JA} is measured in the natural convection at $T_A = 25^{\circ}C$ on a low effective single layer thermal conductivity test board of JEDEC 51-3 thermal measurement standard. Test condition: Device mounted on 2" x 2" FR-4 substrate PCB, 2oz copper, with minimum recommended pad on top layer and thermal vias to bottom layer ground plane.

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DS_SY5861Rev. 0.1



SO8 Package Outline & PCB Layout Design



Notes: All dimensions are in millimeters.

All dimensions don't include mold flash & metal burr.

0.60 - 0.85

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DS_SY5861Rev. 0.1

1.27 (TYP)